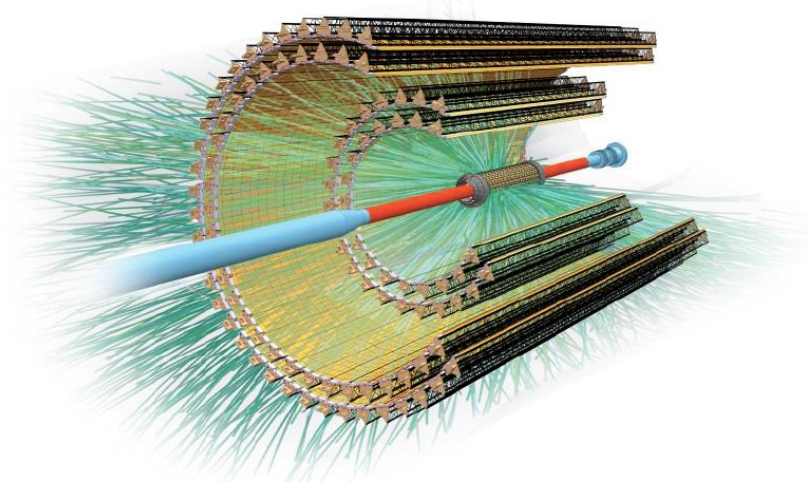


# Update on Pixel Chip for the ALICE ITS Upgrade

Luciano Musa - CERN



*LHCC Week – Detector Upgrade Session  
1<sup>st</sup> December 2015*

# Update on the Pixel Chip for the ALICE ITS Upgrade

A Large Ion Collider Experiment

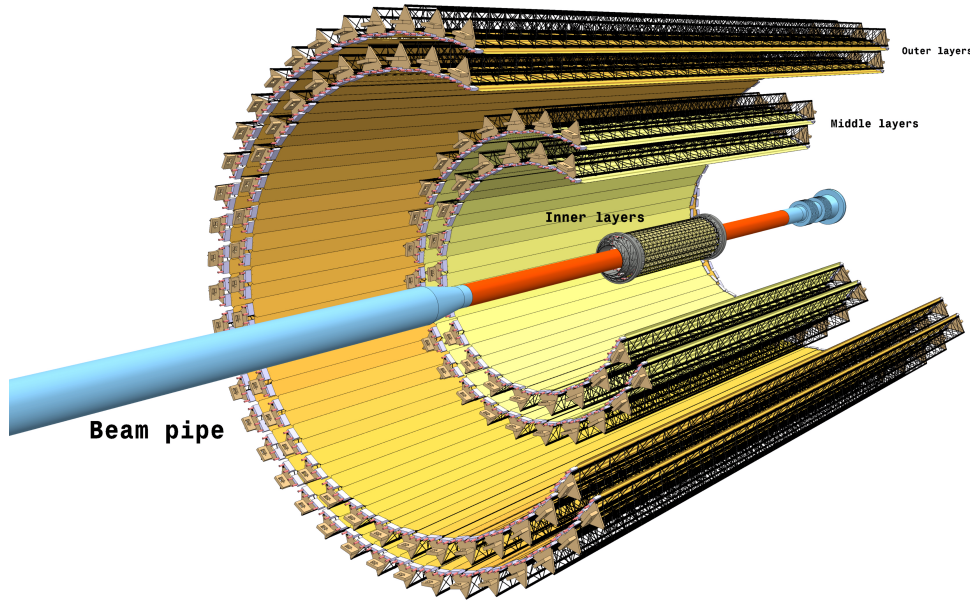


## OUTLINE

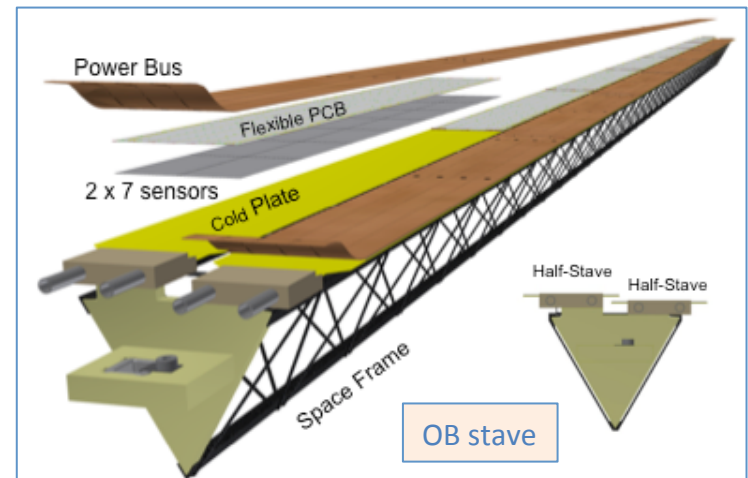
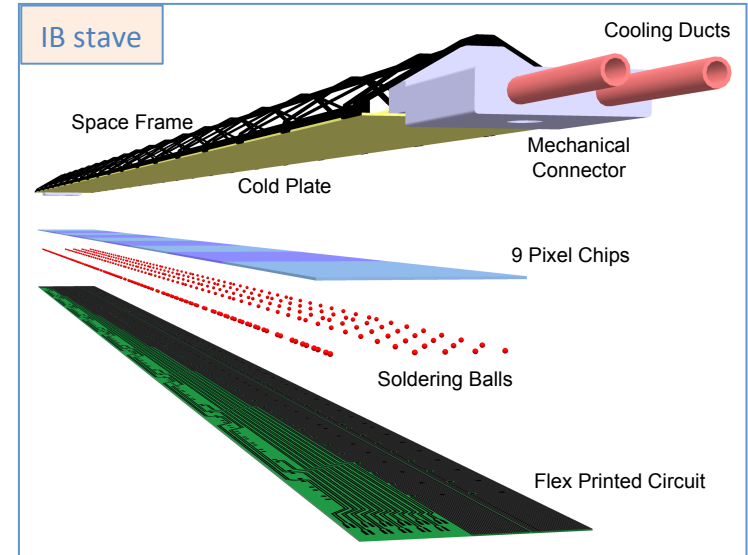
- ⦿ ITS layout and Pixel Chip General Requirements
- ⦿ Pixel Chip (ALPIDE) Overview and Status
- ⦿ pALPIDE-2 Main Design Features and Performance
- ⦿ Engineering Design Review
- ⦿ pALPIDE-3 Preliminary Results
- ⦿ Towards final chip

# New ITS Layout

A Large Ion Collider Experiment



- ▶ 7-layer barrel based on CMOS sensors
- ▶ Radial coverage 22 – 400 mm
- ▶ Total active area  $\sim 10\text{m}^2$
- ▶  $\sim 24,000$  pixel chips (12.5 G pixels)
- ▶ Radiation:  $\sim 2.7$  Mrad ( $\sim 1.7 \times 10^{13}$  1MeV  $n_{\text{eq}}/\text{cm}^2$ ) including safety factor 10



# PIXEL Chip – General Requirements

A Large Ion Collider Experiment



## General Requirements and ALPIDE Specifications<sup>(\*)</sup>

Parameter	Inner Barrel	Outer Barrel
Chip size (mm x mm)	15 x 30	
Chip thickness ( $\mu\text{m}$ )	50	100
Spatial resolution ( $\mu\text{m}$ )	5	10 (5)
Detection efficiency	> 99%	
Fake hit rate	< $10^{-5} \text{ evt}^{-1} \text{ pixel}^{-1}$ (>> ALPIDE)	
Integration time ( $\mu\text{s}$ )	< 30 (< 10)	
Power density ( $\text{mW}/\text{cm}^2$ )	< 300 (~35)	< 100 (~20)
TID radiation hardness (krad) <sup>(*)</sup>	2700	100
NIEL radiation hardness ( $1\text{MeV } n_{\text{eq}}/\text{cm}^2$ ) <sup>(**)</sup>	$1.7 \times 10^{13}$	$1.7 \times 10^{12}$

<sup>(\*)</sup> Colour code: ALPIDE specifications if different from requirements

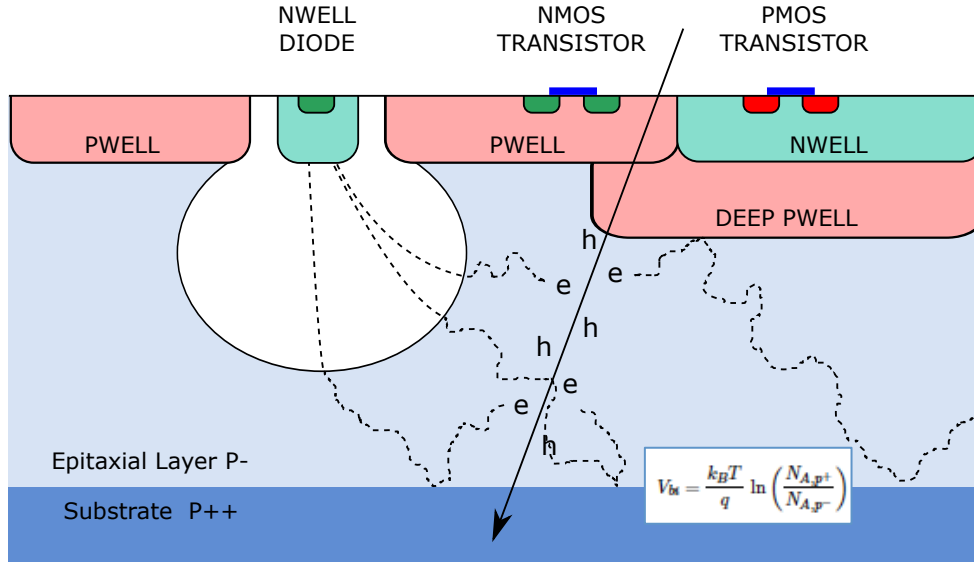
<sup>(\*\*)</sup> 10 x radiation load integrated over approved programme (~ 6 years of operation)

# ITS Pixel Chip – technology choice

A Large Ion Collider Experiment



## CMOS Pixel Sensor using TowerJazz 0.18μm CMOS Imaging Process

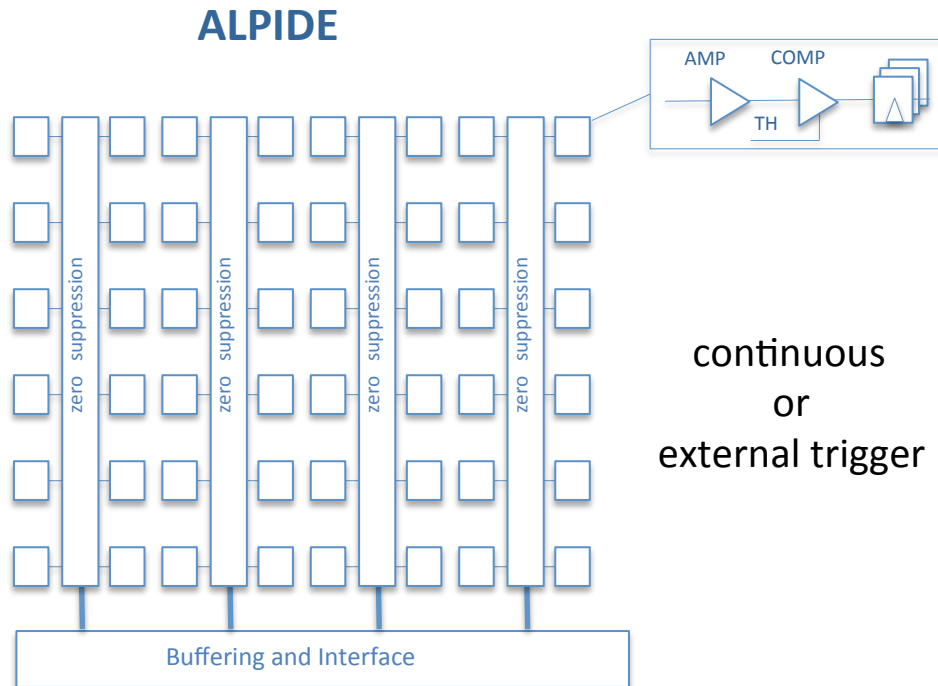


### Tower Jazz 0.18 μm CMOS

- feature size 180 nm
- metal layers 6
- gate oxide 3nm

substrate:  $N_A \sim 10^{18}$   
epitaxial layer:  $N_A \sim 10^{13}$   
deep p-well:  $N_A \sim 10^{16}$

- ▶ High-resistivity ( $> 1\text{k}\Omega\text{ cm}$ ) p-type epitaxial layer ( $18\mu\text{m}$  to  $30\mu\text{m}$ ) on p-type substrate
- ▶ Small n-well diode ( $2\mu\text{m}$  diameter),  $\sim 100$  times smaller than pixel  $\Rightarrow$  low capacitance
- ▶ Application of (moderate) reverse bias voltage to substrate (contact from the top) can be used to increase depletion zone around NWELL collection diode
- ▶ Deep PWELL shields NWELL of PMOS transistors to allow for full CMOS circuitry within active area



## Architecture

- ▶ In-pixel amplification
- ▶ In-pixel discrimination
- ▶ In-pixel (multi-) hit buffer
- ▶ In-matrix sparsification

## Key Features

- ⦿ 28  $\mu\text{m}$  x 28 mm pixel pitch
- ⦿ Continuously active, ultra-low power front-end (40nW/pixel)
- ⦿ No clock propagation to the matrix  $\rightarrow$  ultra-low power matrix readout (2mW whole chip)
- ⦿ Global shutter (<10 $\mu\text{s}$ ): triggered acquisition or continuous

# ALPIDE Development

A Large Ion Collider Experiment

2012

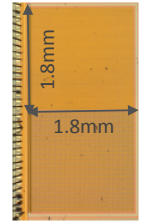
Explorer

- $20\mu\text{m} \times 20\mu\text{m}$  and  $30\mu\text{m} \times 30\mu\text{m}$  pixels (analogue readout)
- pixel geometry, starting material, sensitivity to radiation

2013

pALPIDEss-0

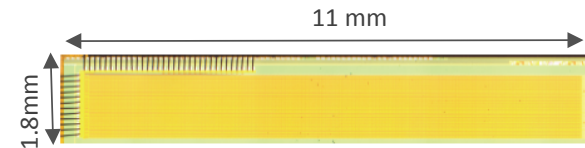
- Matrix with 64 columns x 512 rows
- $22\mu\text{m} \times 22\mu\text{m}$  pixels
- (in-pixel discrimination and buffering)
- zero suppression within pixel matrix



May-2014

pALPIDE-1

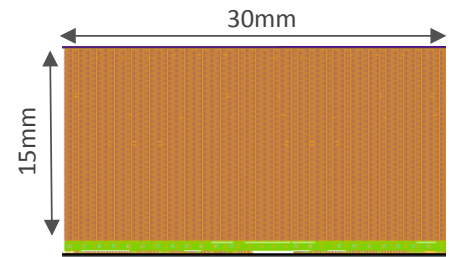
- **Full-scale prototype: 1024 x 512**
- 4 sectors with different pixels
- pixel pitch:  $28\mu\text{m} \times 28\mu\text{m}$
- 1 register/pixel, no final interface



May-2015

pALPIDE-2

- Optimization of several circuit blocks
- final interface: allows integration into ITS modules
- NO high-speed output link (1.2 Gbit/sec replaced by a 40Mb/s)



Oct-2015 Design Review

Oct-2015

pALPIDE-3

- 8 sectors with different pixel variants, 3 registers / pixel
- Final interfaces, more features including 1.2 Gbit/s output serial link
- Some optimization for yield improvement
- Characterization ongoing

# pALPIDE-1&2 – Main Design Features

A Large Ion Collider Experiment



ALPIDE full-scale prototypes vers. 1 (2014) and ver.2 (2015)

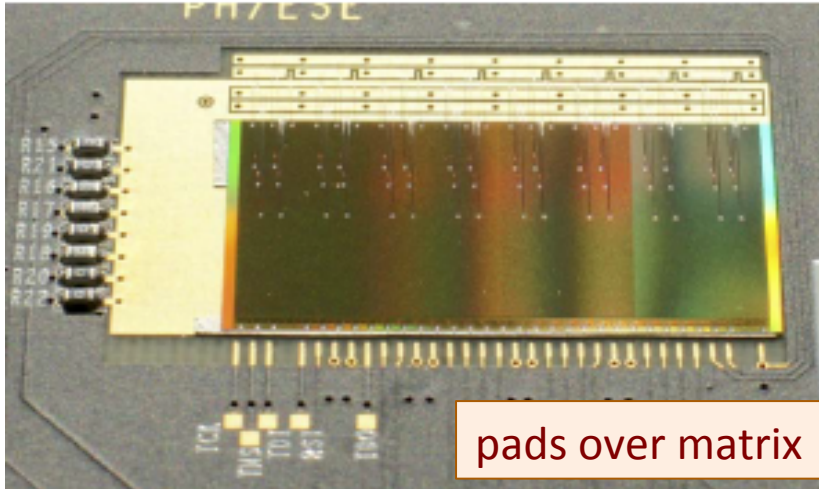


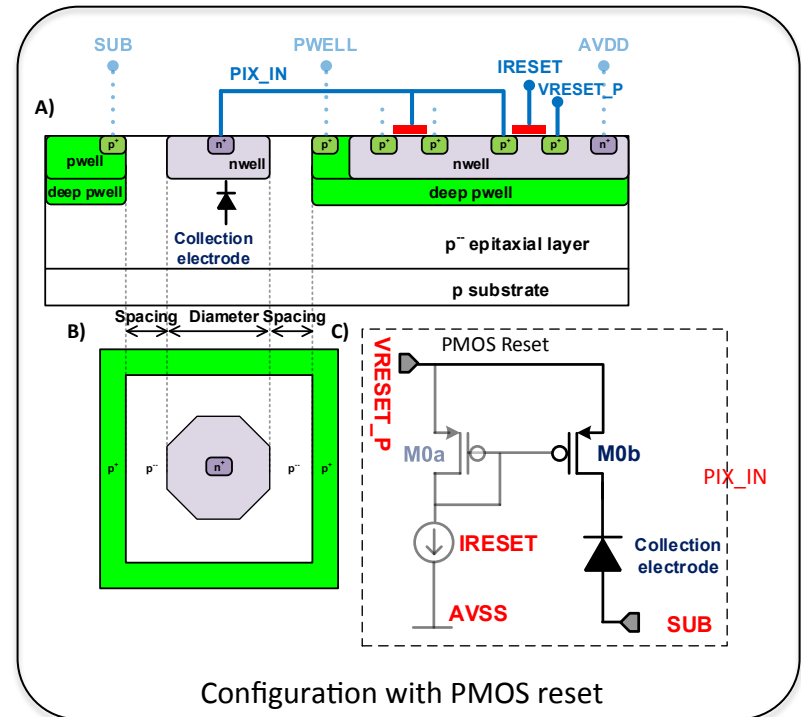
Figure: picture of pALPIDE-2

## Main parameters

- Dimensions: 30mm x 15 mm
- Pixel Matrix: 1024 cols x 512 rows
- Pixel pitch:  $28\mu\text{m} \times 28\mu\text{m}$
- Integration time:  $<10\mu\text{s}$
- Power consumption:  $<40\text{mW}/\text{cm}^2$
- 4 sectors with different pixels

Matrix divided in 4 sectors, each with 256 cols x 512 rows

- Collection node: octagonal  $2\mu\text{m}$  diameter
- Spacing NWELL and PWELL:  $2\mu\text{m}$  to  $4\mu\text{m}$
- 2 reset mechanism: diode, PMOS
- 1 sector with larger (x2) input transistor



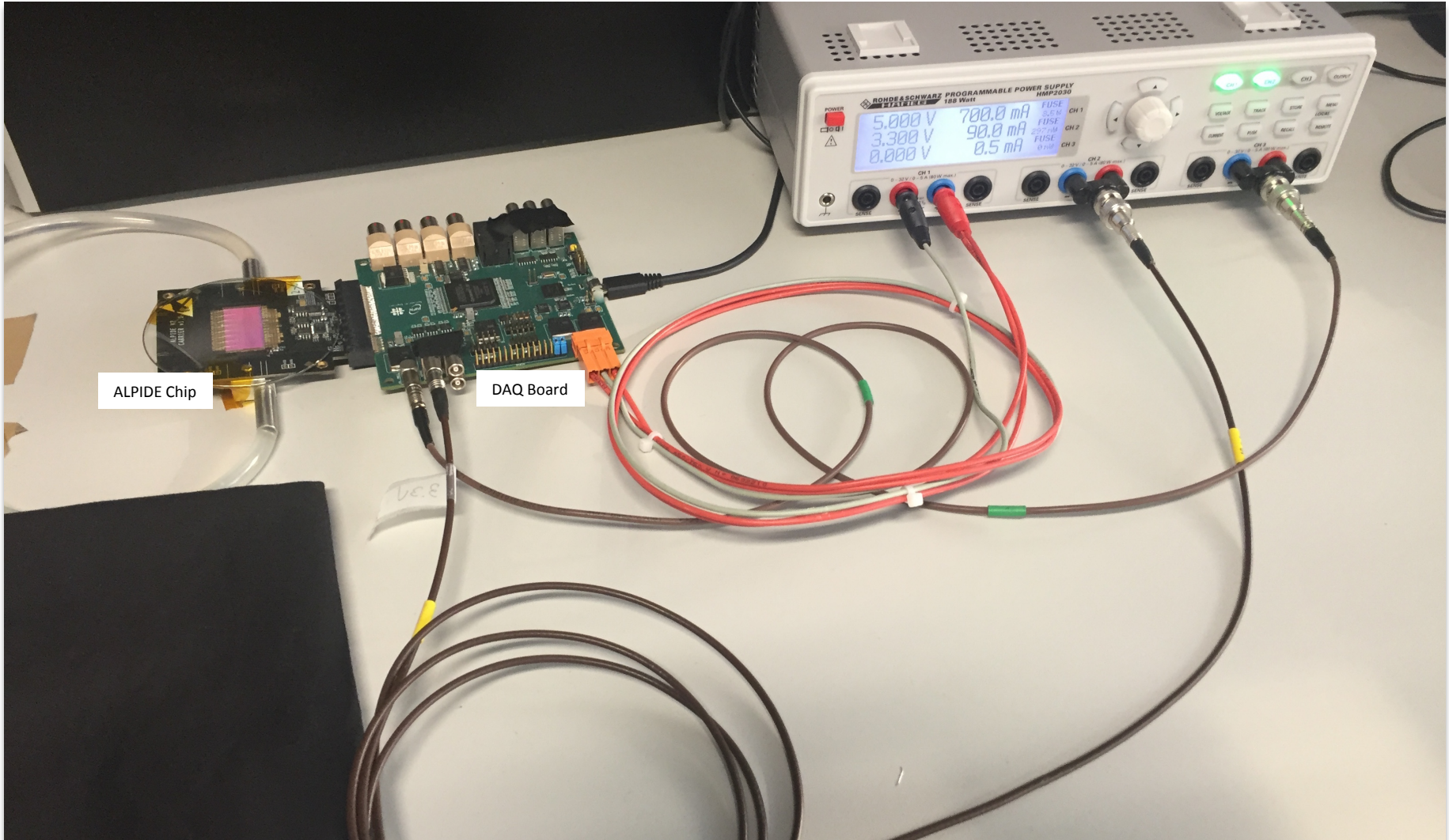


# Experimental Results

A Large Ion Collider Experiment



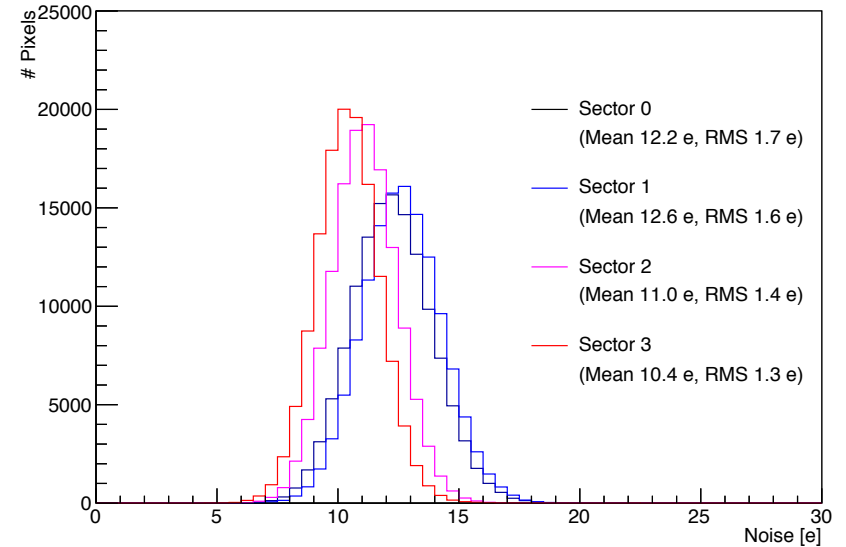
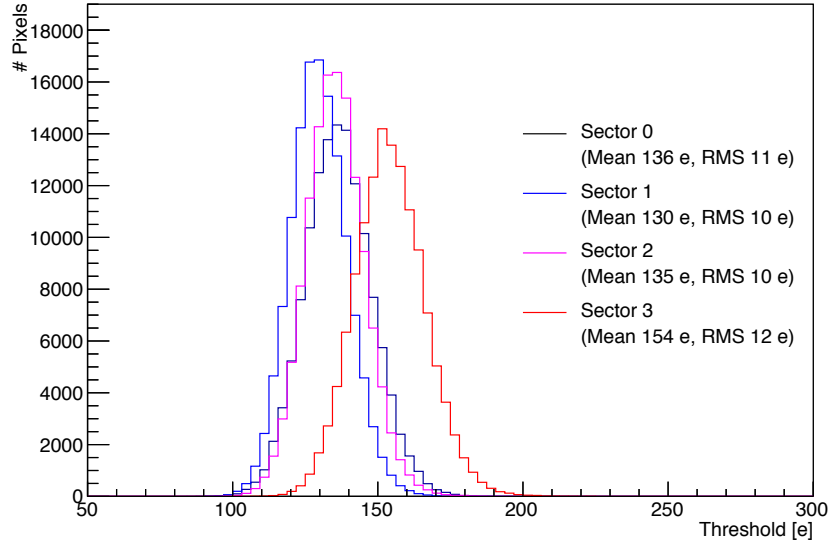
Laboratory Measurements → e.g. noise and thresholds



ALPIDE Chip

DAQ Board

## Example of Threshold and Noise Distributions

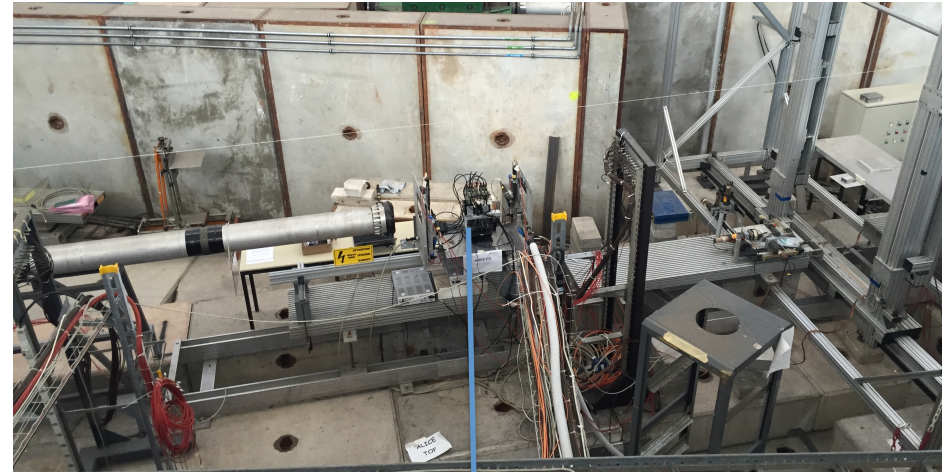


$$V_{\text{SUB}} = -3\text{V}, I_{\text{THR}} = 0.5\text{nA}, V_{\text{CASN}} = 0.95\text{V}$$

- ▶ All sectors behave qualitatively similarly
- ▶ Noise is about the same value as threshold RMS
- ▶ Threshold about 10 x higher than noise
- ▶ Threshold 7 x smaller than most-probable energy loss signal of a MIP in 18 $\mu\text{m}$  of silicon

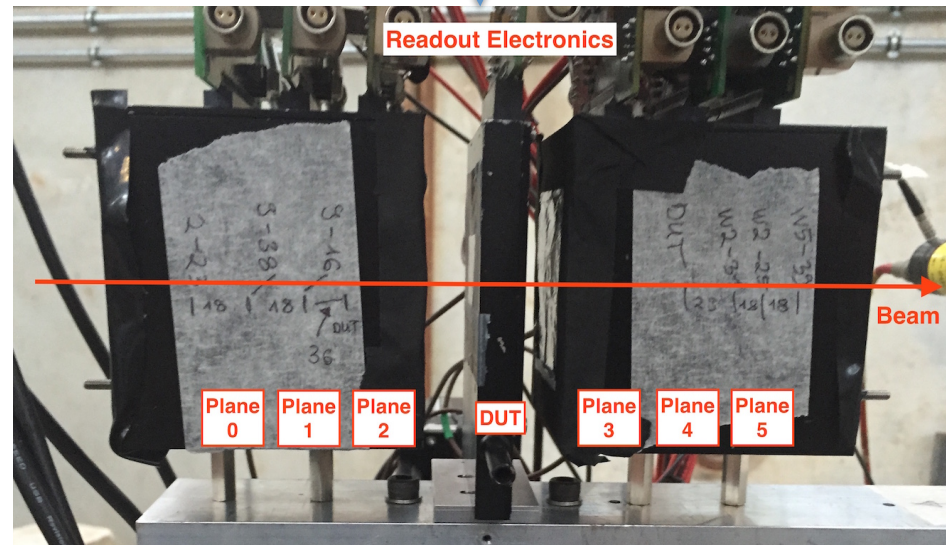
## Test Beam Set-up

- ▶ 6 GeV/c  $\pi^-$  beam at CERN PS
- ▶ 6 reference planes based on pALPIDE-1
- ▶ Single pALPIDE-2 as Device Under Test (DUT) in the center
- ▶ Track resolution of about  $2.8\mu\text{m}$  ( $\ll 28\mu\text{m}$ )



## Analysis Method

- ▶ Extrapolate track from reference planes through DUT
- ▶ Search for clusters next to extrapolated impinging point  $\rightarrow$  detection efficiency
- ▶ Obtain cluster size
- ▶ Compare extrapolated and actual position  $\rightarrow$  position resolution



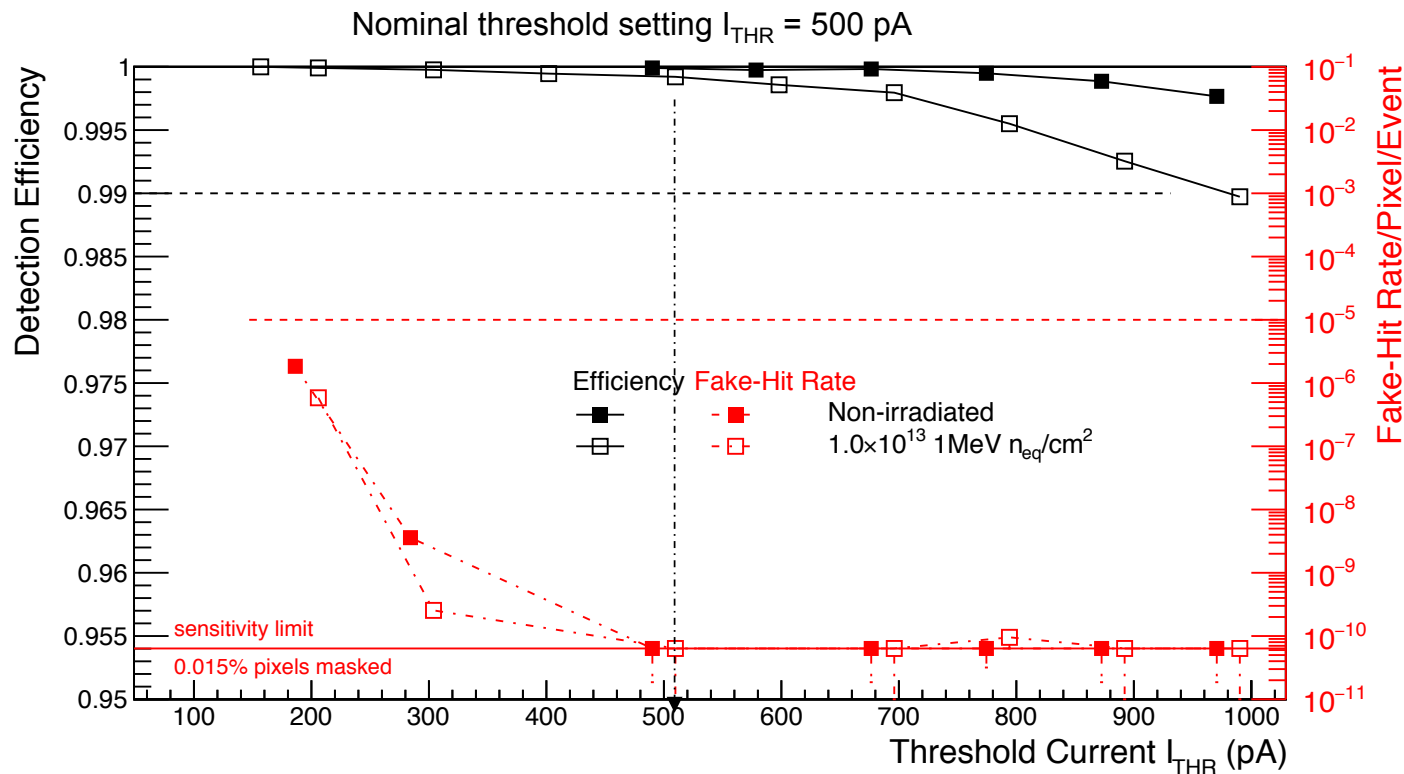
# Experimental Results – pAlpide-2

A Large Ion Collider Experiment



## Efficiency and fake hit rate

$\text{epi}=25\mu\text{m}$ ,  $V_{\text{BB}}=-6\text{V}$ ,  $\text{spacing}=2\mu\text{m}$



$\epsilon_{\text{det}} > 99\%$  @  $\lambda_{\text{fake}} \ll 10^{-5} / \text{event/pixel}$   $\rightarrow$  large margin over design requirements

- Results refer to chips with  $25\mu\text{m}$  high-res epi layer, thinned to  $50 \mu\text{m}$ :  
1 non irradiated and 1 irradiated with  $10^{13} \text{ 1MeV } n_{\text{eq}} / \text{cm}^2$

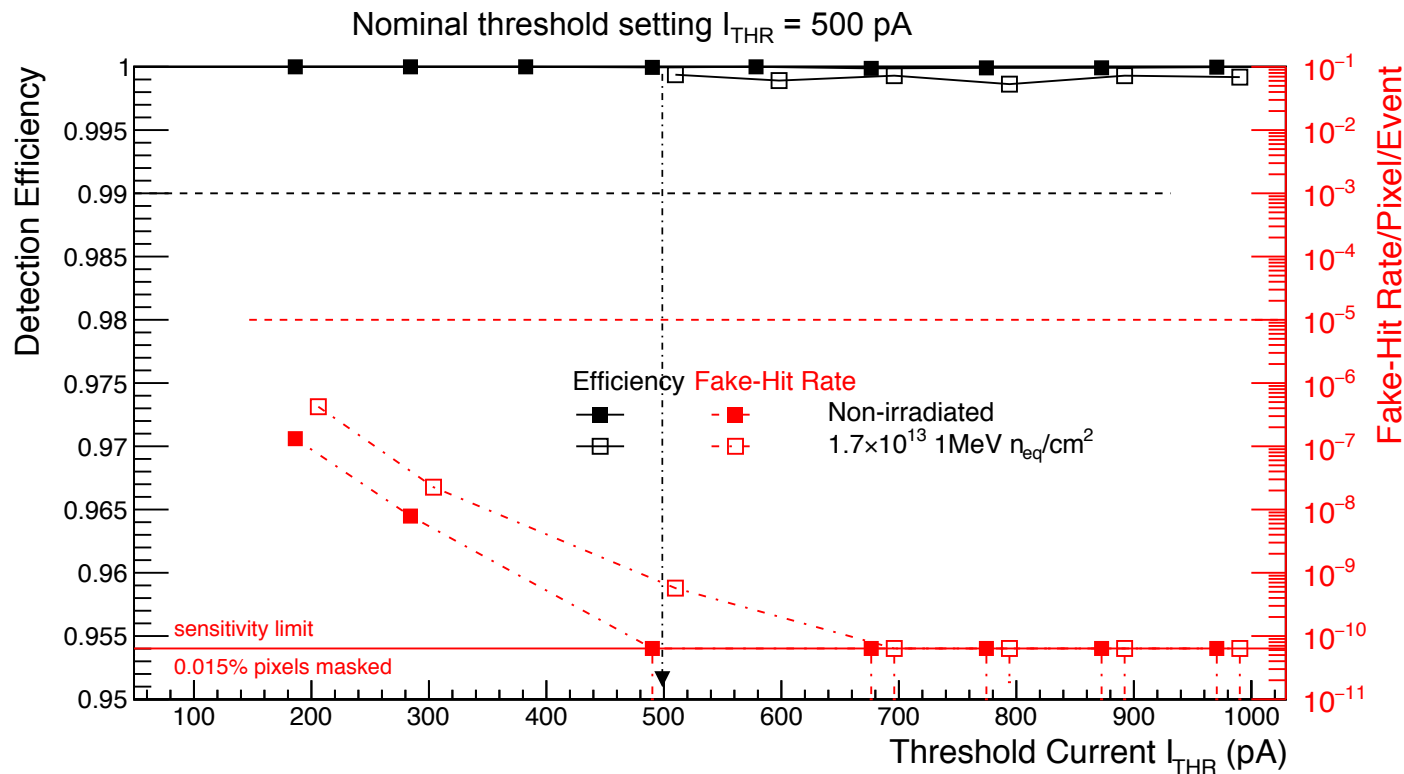
# Experimental Results – pAlpide-2

A Large Ion Collider Experiment



## Efficiency and fake hit rate

$\text{epi}=30\mu\text{m}$ ,  $V_{\text{BB}}=-6\text{V}$ ,  $\text{spacing}=4\mu\text{m}$

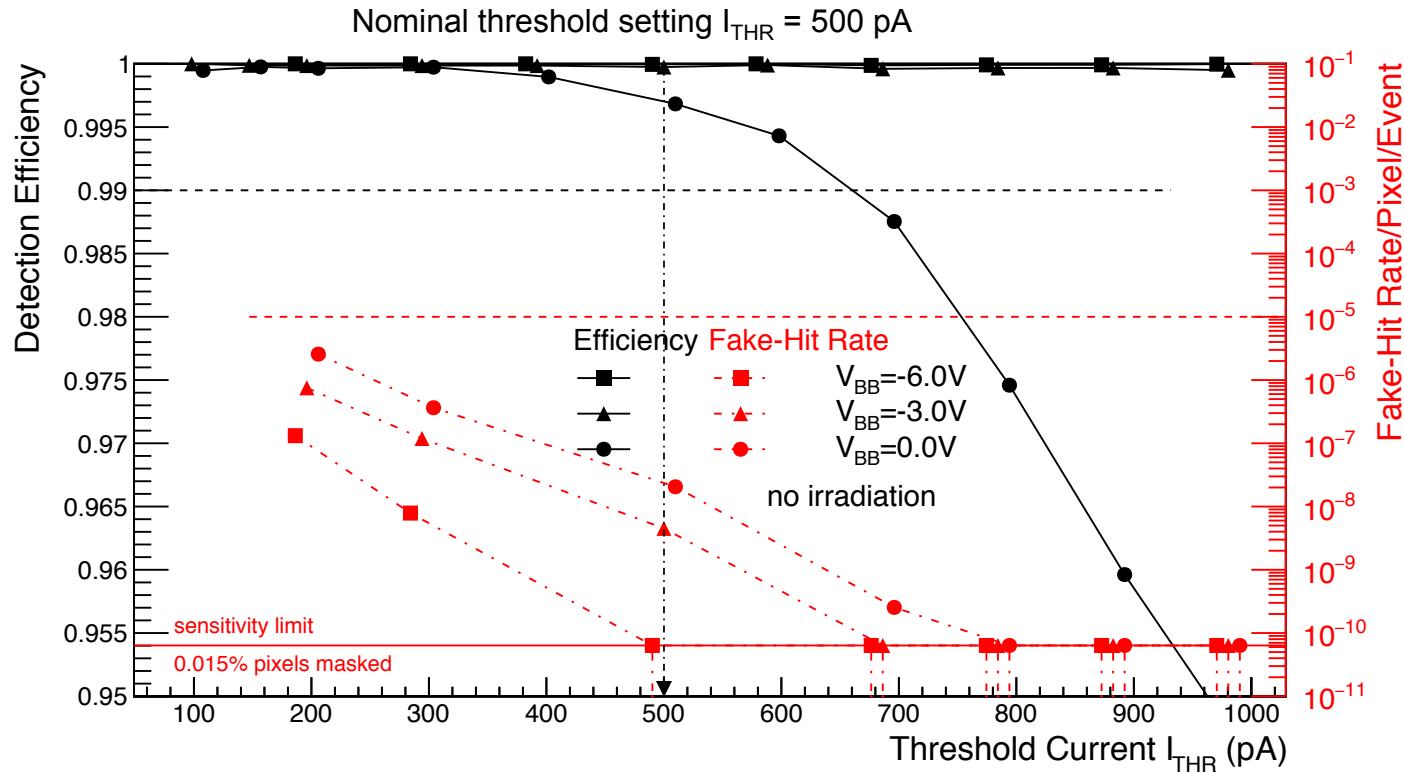


Even larger operation margin for  $30\mu\text{m}$  epi layer and  $4\mu\text{m}$  spacing

- Results refer to chips with  $30\mu\text{m}$  high-res epi layer, thinned to  $50 \mu\text{m}$ :  
1 non irradiated and 1 irradiated with  $10^{13} \text{ 1MeV } n_{\text{eq}} / \text{cm}^2$

## Efficiency and fake hit rate

epi=30 $\mu$ m, spacing=4 $\mu$ m

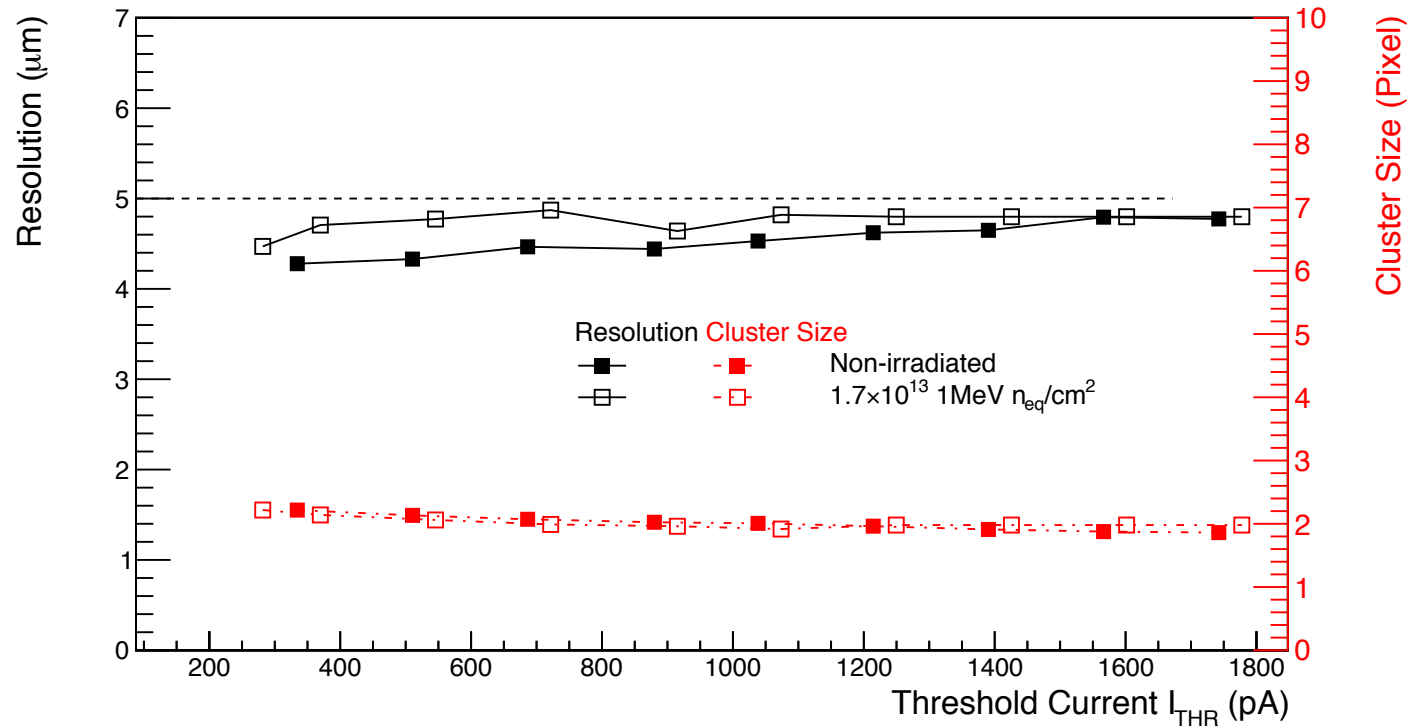


operation margin significantly increased reverse bias voltage

- Results refer to chips with 30 $\mu$ m high-res epi layer, thinned to 50  $\mu$ m

## Spatial Resolution and Cluster Size

$\text{epi}=30\mu\text{m}$ ,  $V_{\text{BB}}=-6\text{V}$ ,  $\text{spacing}=4\mu\text{m}$



$\sigma_{\text{det}} \approx 5 \mu\text{m}$  is achieved before and after irradiation

- Results refer to chips with  $30\mu\text{m}$  high-res epi layer, thinned to  $50 \mu\text{m}$   
1 non irradiated and 1 irradiated with  $1.7 \times 10^{13}$  1MeV  $n_{\text{eq}} / \text{cm}^2$



EDR (19 Oct 2015) - Review panel: A. Marchioro (CERN), W. Mueller (GSI), X. Llopart (CERN)

## General Assessment

“The reviewers were impressed by the amount and the quality of information provided by the design team for the review. The design team has clearly worked very hard and thoroughly for this project and was orchestrated very competently and effectively by its management team.

The Alice ITS project aims at introducing some very original solutions in the area of pixelated detectors for particle physics, in particular the new technology, the sensor architecture, the extremely low power front-end circuitry and the mechanical thinning of the detector, all are pioneering significant innovations.

Unavoidably innovations cannot be decoupled from risks, but it seems to these reviewers that the team has studied in detail the various aspects of the design of the proposed chip and has used extensively simulation tools to understand its behavior. Of course the usage of simulation tools must be accompanied by and the results digested with a fair amount of common sense, which has been expressed during the review. The engineering team has shown to have worked proactively on a number of issues that were raised during the presentation.

It is also fair to notice that the learning in a new and very promising monolithic technology that this project will hopefully bring to the HEP community does by itself partly justify the risk taken with the project.

Finally, it was really a pleasure to see the enthusiasm and competence of the overall team working on this project.”



## First Laboratory Results

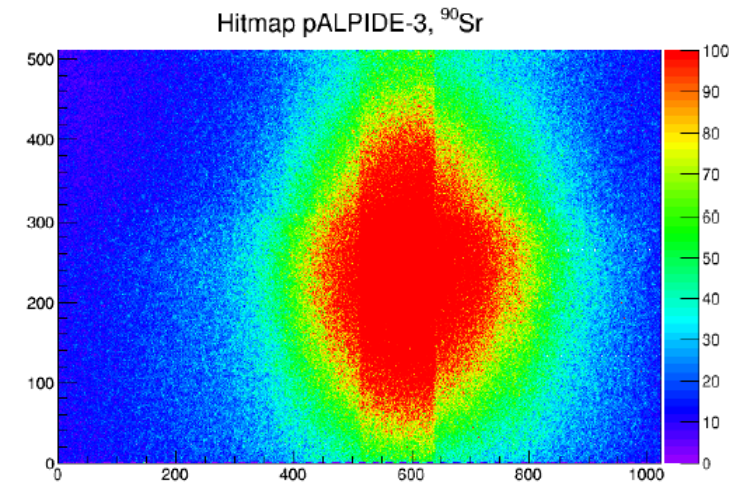
- ▶ 29 chips mounted on carrier boards (12 x 18 $\mu$ m, 8 x 25 $\mu$ m, 9 x 30 $\mu$ m)
- ▶ 4 chips non working (still to verify whether is the chip or the assembly)
- ▶ 25 chips are working in standard tests (→ 86% yield)

## Irradiation tests

- ▶ Chips irradiated with neutrons and ionizing radiation
- ▶ Done first campaign of SEU/SEL measurements

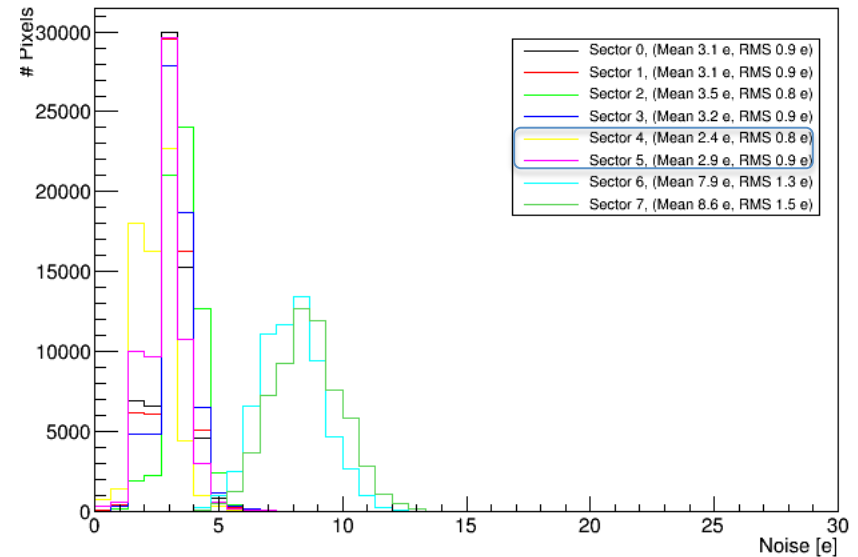
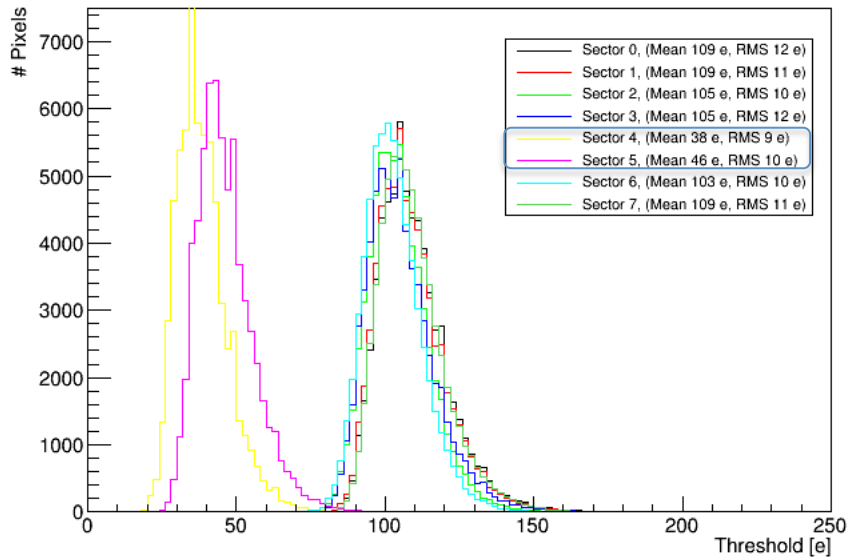
## Test beam

- ▶ Only 1 day of test beam at the PS
- ▶ Few measurements on one chip (18 $\mu$ m,  $V_{SUB}=0$ )
- Systematic test ongoing in laboratory
- Next test beam in Frascati starting on 7 December



following slides show some very partial and preliminary results

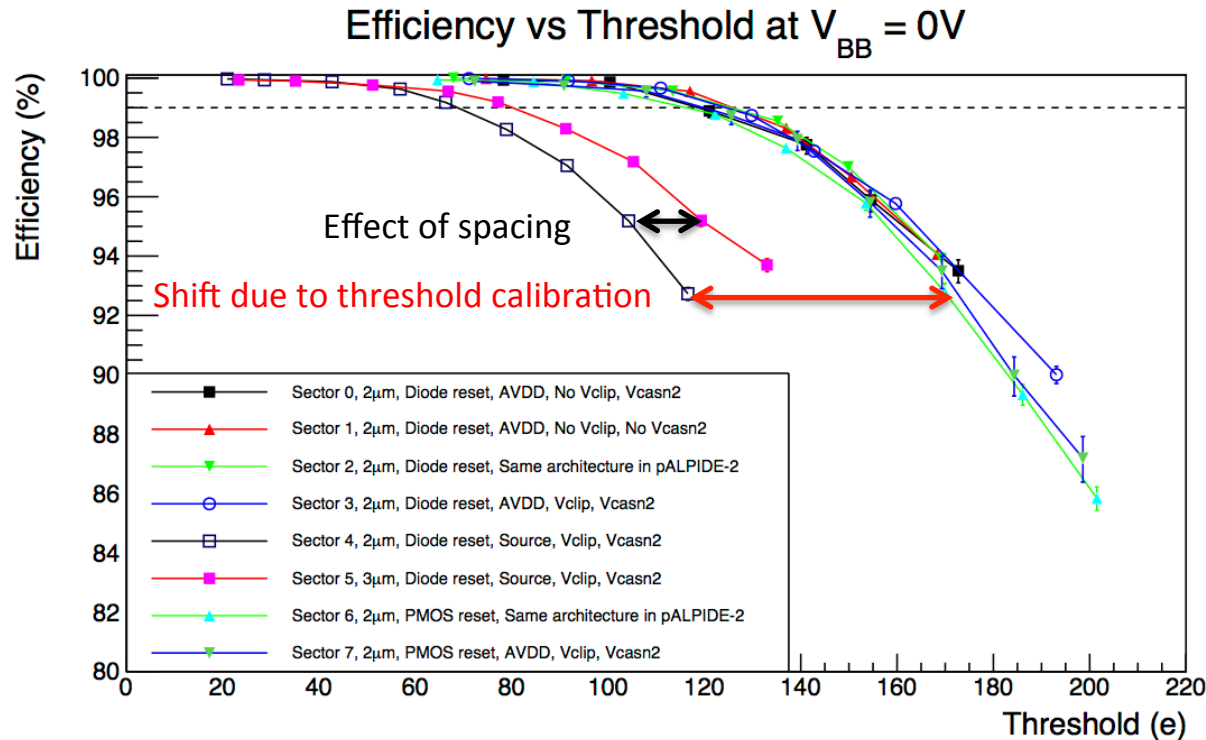
## Example of Threshold and Noise Distributions



- ▶ Thresholds (left) and Noise (right) distributions for all sectors (ITRH=51)
- ▶ Sector 4 and 5 show lower thresholds due to (expected) higher gain
- ▶ Sector 6 and 7 PMOS reset, all others diode reset

## pALPIDE-3 PS test beam

- ▶ 1 chip tested for one day (last day of PS test beam)
- ▶ Measurements with NO reverse bias voltage



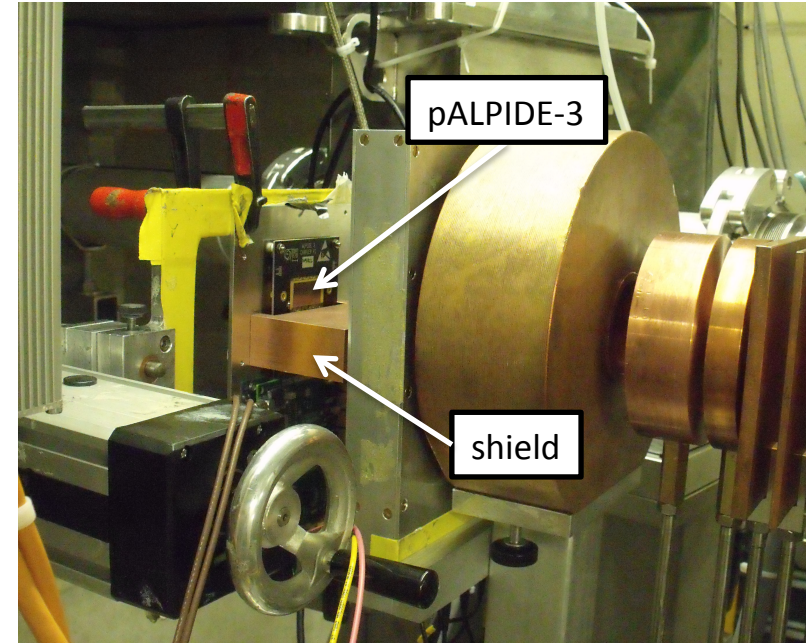
# Experimental Results – pALPIDE-3

A Large Ion Collider Experiment

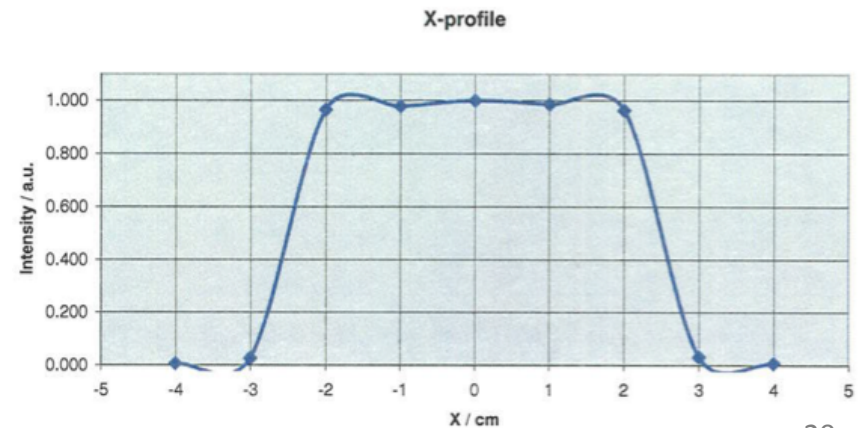
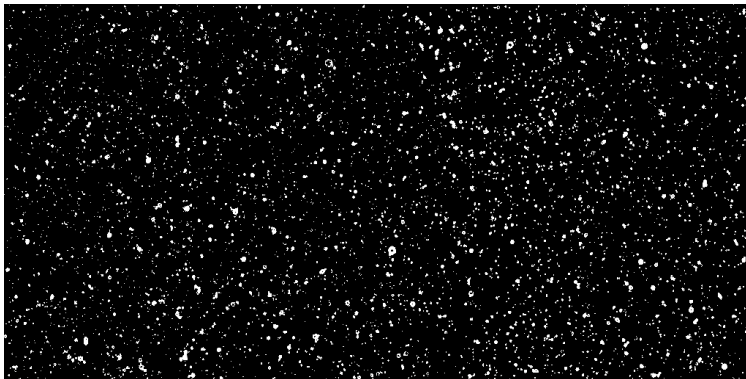


## Single Event Upset - Setup

- Proton Irradiation Facility (PIF) @ PSI
- 200 MeV protons
- $1.6 \times 10^8$  p/cm<sup>2</sup>
- Widened beam to cover full pALPIDE-3 chip
- Chip connected to standard readout system
- Cross-sections measured by digitally stimulating the pixels
- Unmasking cross-section verified by looking at beam particles

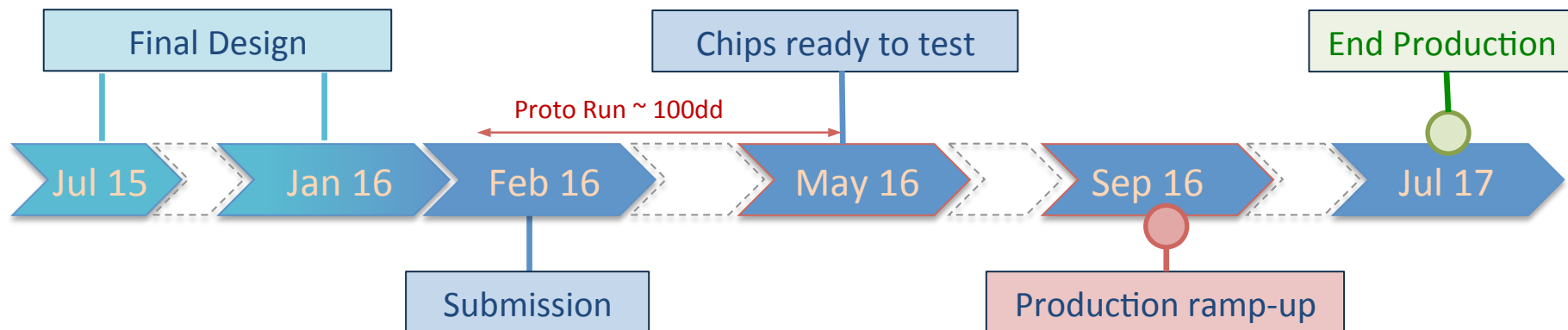


## Picture of one event (w/o masking)



# ALPIDE Finalization and Production

A Large Ion Collider Experiment



## ALPIDE finalization and production timeline

- ▶ Engineering Design Review: Oct 15
- ▶ Complete design of final ALPIDE: Jan 16
- ▶ Proto-run: Feb – May 16
- ▶ **Production Readiness Review: July 16**
- ▶ Series Production (~25 wafer/week): Sep 16 – Jul 17

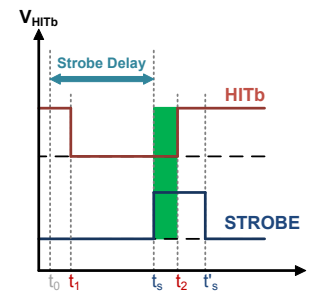
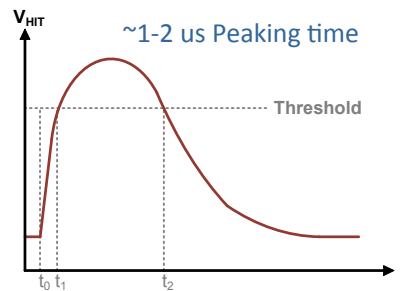
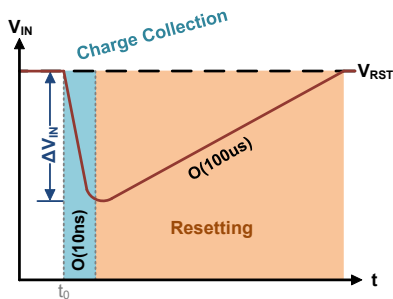
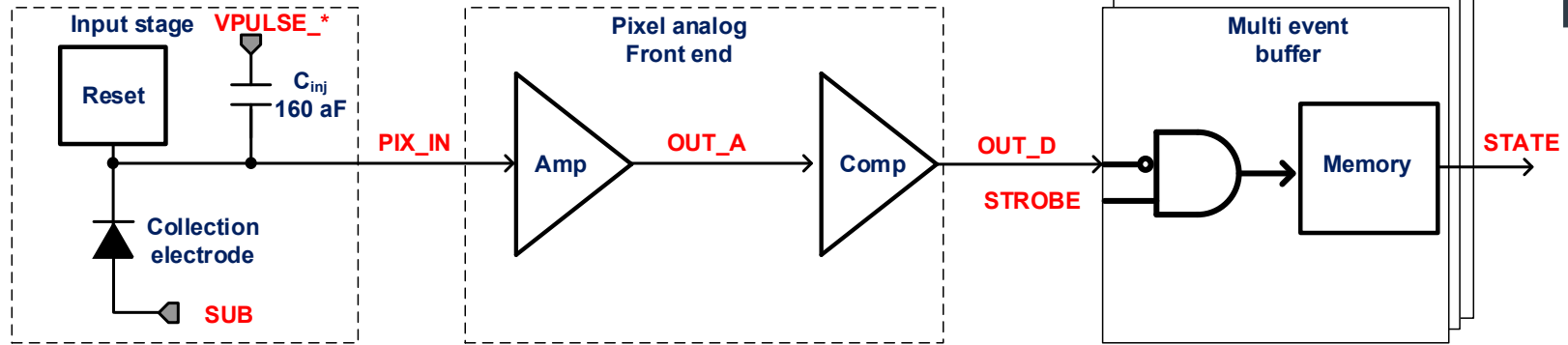
# Spare Material

## Main Design Activities (changes) wrt pALPIDE-3 (including EDR recommendations)

- ▶ Select **final pixel** (collection diode + front-end circuit)
- ▶ Improve detailed routing of pixel configuration control wires under Pads Over Circuits
- ▶ Improve handling of pixel configuration signals from periphery (EDR rec.)
  - Enable fast reload of pixel mask even during readout. Support active forcing of the mask bits from periphery
- ▶ Optimize distribution of global STROBING and PULSING signals from periphery (EDR recommendation)
  - Enable major speed-up of pixel tests with analogue scans and charge injection
  - Optimize supply current time profile (phase shift pulses in time) (EDR rec.)
- ▶ Power optimization of digital block (clock gating)
- ▶ Data Transmission Unit: power optimization
- ▶ MLVDS: experimental verification of new version with module power off protection
- ▶ I/O CMOS: re-simulation to evaluate signal integrity (EDR recommendation)
- ▶ POWER-ON RESET: triplication (together with global reset signals) (EDR recommendation)

# ALPIDE Principle of Operation

A Large Ion Collider Experiment

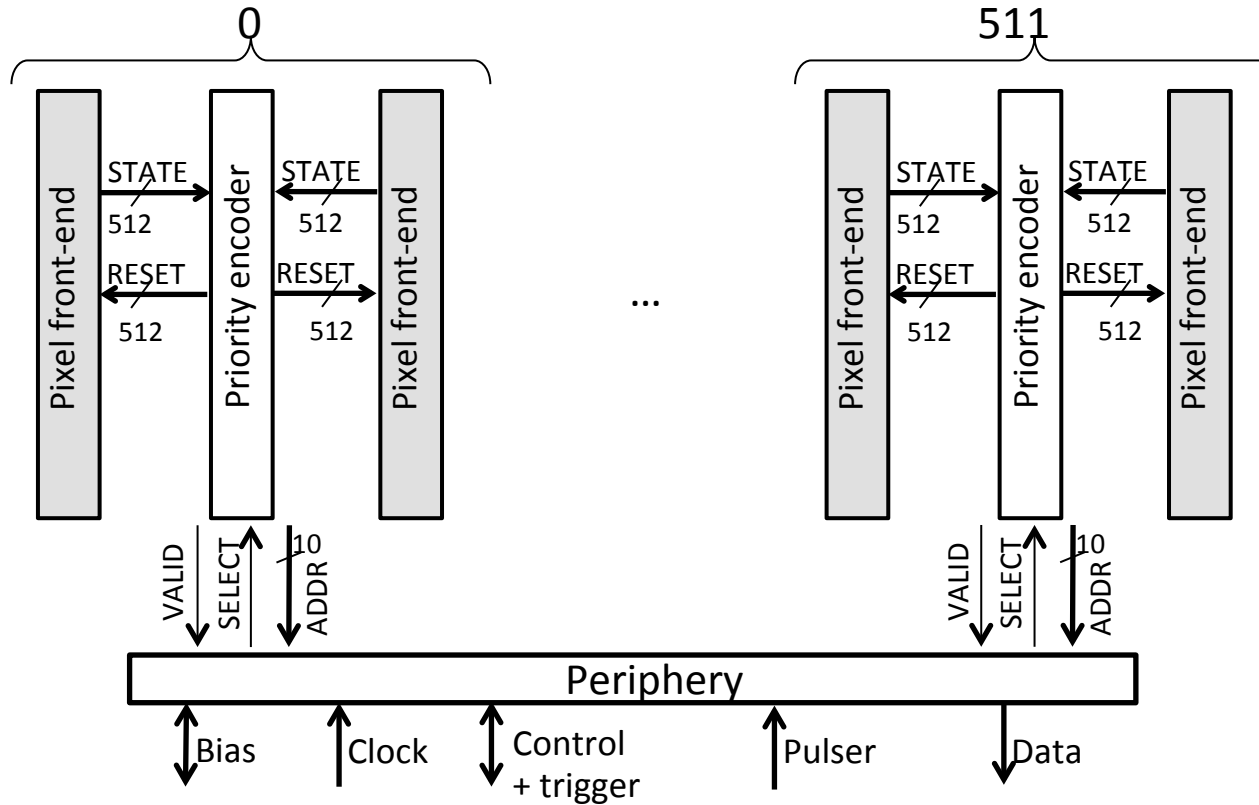


## Front-end acts as delay line

- Sensor and front-end continuously active
- Upon particle hit front-end forms a pulse with  $\sim 1\text{-}2\mu\text{s}$  peaking time
- Threshold is applied to form binary pulse
- Hit is latched into a (3-bit) memory if strobe is applied during binary pulse

ultra low-power front-end circuit  
40nW / pixel





## Pixel Matrix - Hit driven architecture

low-power matrix readout ~ 2mW

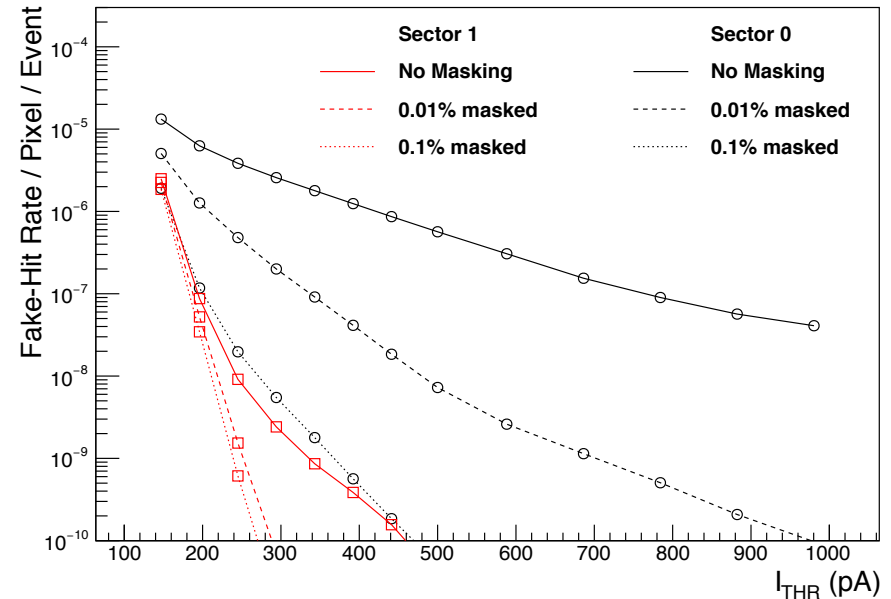
- Priority encoder sequentially provides addresses of all hit pixels present in double column
- No activity if no hit (**no free running clock**) → **low power**

## Fake-Hit Rate Measurements

- ▶ 120,000 (pseudo) random triggers
- ▶ No external signal
- ▶ Offline masking of 0.15% of the hottest pixels (20 per sector)
- ▶ Measurement reach / sensitivity limit

$$p_{\min} = \frac{1}{N_{\text{Event}} \cdot N_{\text{Pixel}}}$$
$$= 6.36 \cdot 10^{-11} / \text{Pixel} / \text{Event}$$

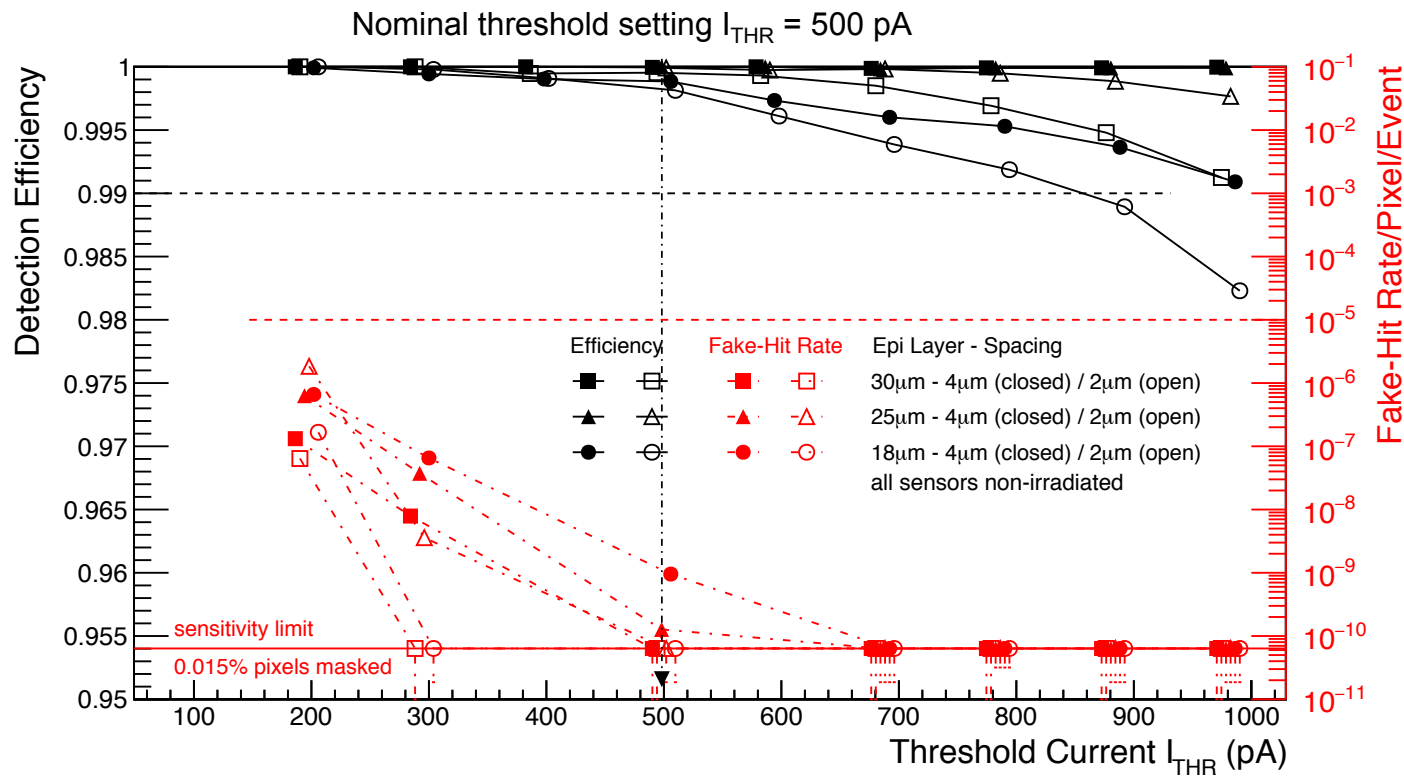
- ▶ Larger size input transistor (sector 1) reduces fake-hit rate significantly



8 chips,  $V_{\text{SUB}} = -3\text{V}$ ,  $I_{\text{THR}} = 0.5\text{nA}$ ,  $V_{\text{CASN}} = 0.95\text{V}$

## Efficiency and Fake Hit Rate

$V_{BB} = -6V$



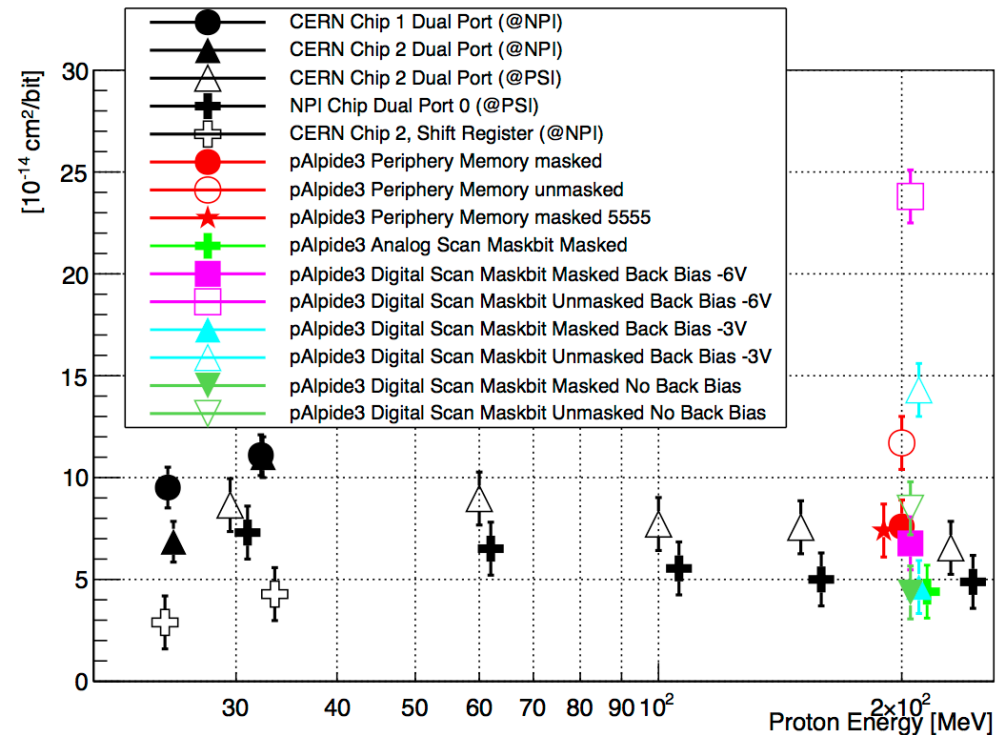
Larger "spacing" shows better detection efficiency

- Results refer to chips with 30µm high-res epi layer, thinned to 50 µm

## Single Event Upset - Results

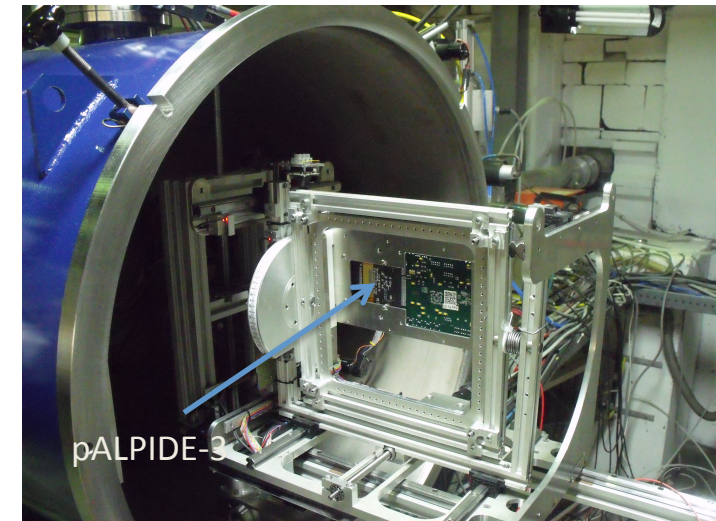
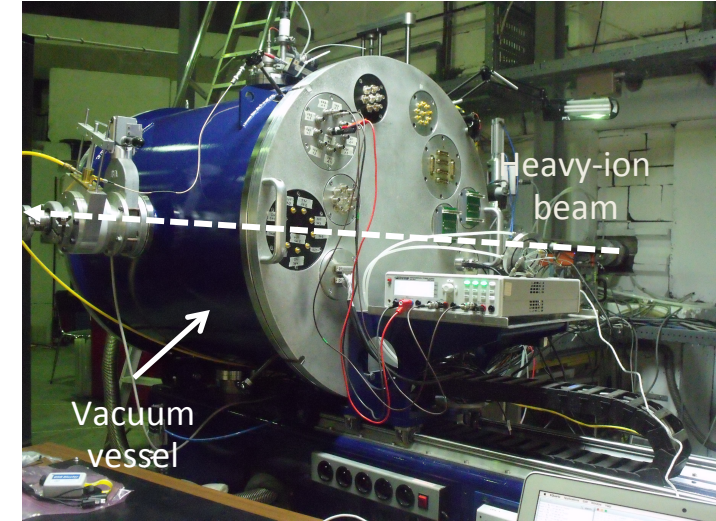
- Cross-sections of data memories validated:  
 $\sigma_{DP} \approx (4-8) \times 10^{-14} \text{ cm}^2/\text{bit}$
- Cross-section of mask register comparable to standard-cell version:  
 $\sigma_{FF,0V} \approx (4-8) \times 10^{-14} \text{ cm}^2/\text{bit}$   
 (at 0V back-bias)
- Cross-section increases with back-bias.  
 Upper limit:

$$\sigma_{FF,6V} < 2.5 \times 10^{-13} \text{ cm}^2/\text{bit}$$



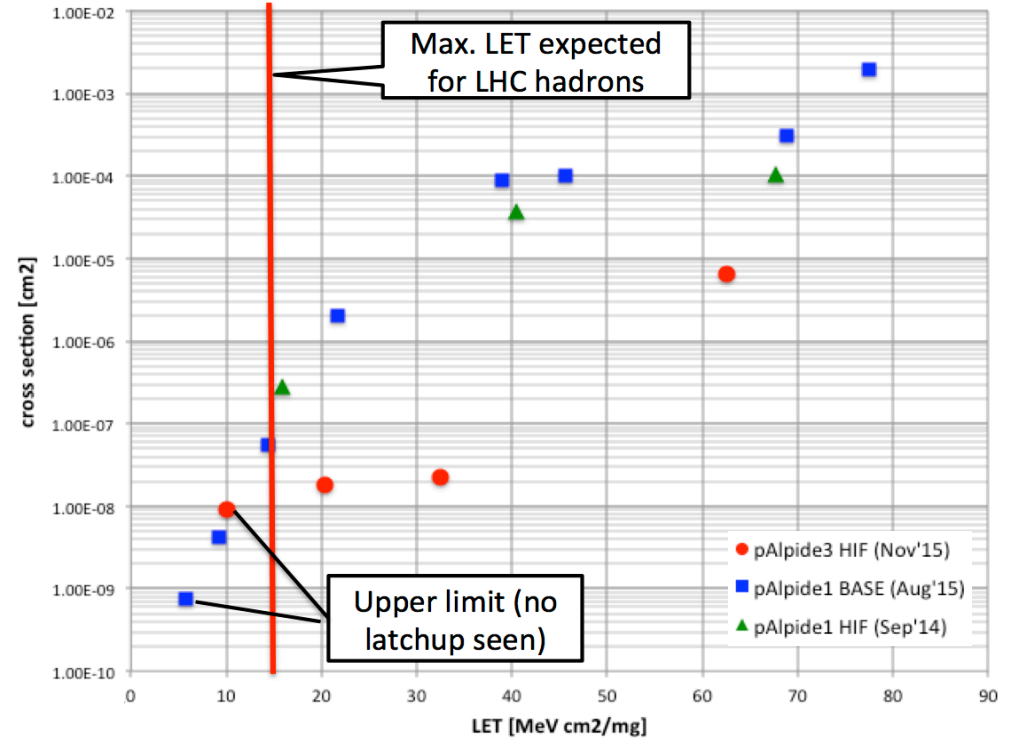
## Single Event Latchup - Setup

- Heavy Ion Irradiation Facility (**HIF**) at Louvain-La-Neuve
- Particle flux:  $10^4/\text{cm}^2/\text{s}$
- LETs: 10.0, 20.4, 32.5, and 62.5 MeV  $\text{cm}^2/\text{mg}$
- First test: no back-bias



## Single Event Latchup – Preliminary Results

- Analogue latch-up (present in pALPIDE-1) have disappeared as effect of the modifications implemented
- Cross-section reduced by 1-4 orders of magnitude



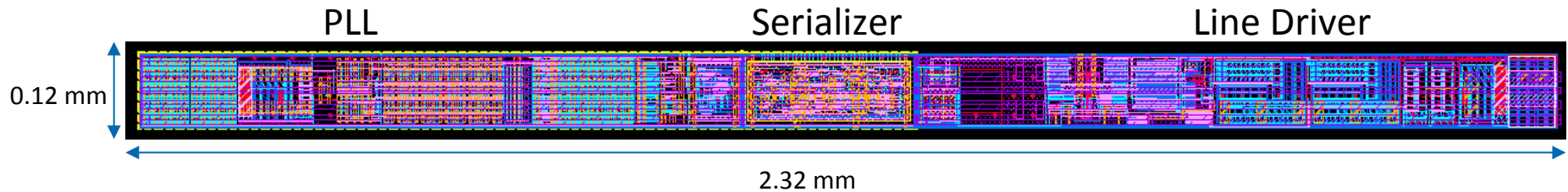
## DTU – Data Transmission Unit (HSO)

### DTU v2b

Implemented in **pALPIDE-3** (June 2015)

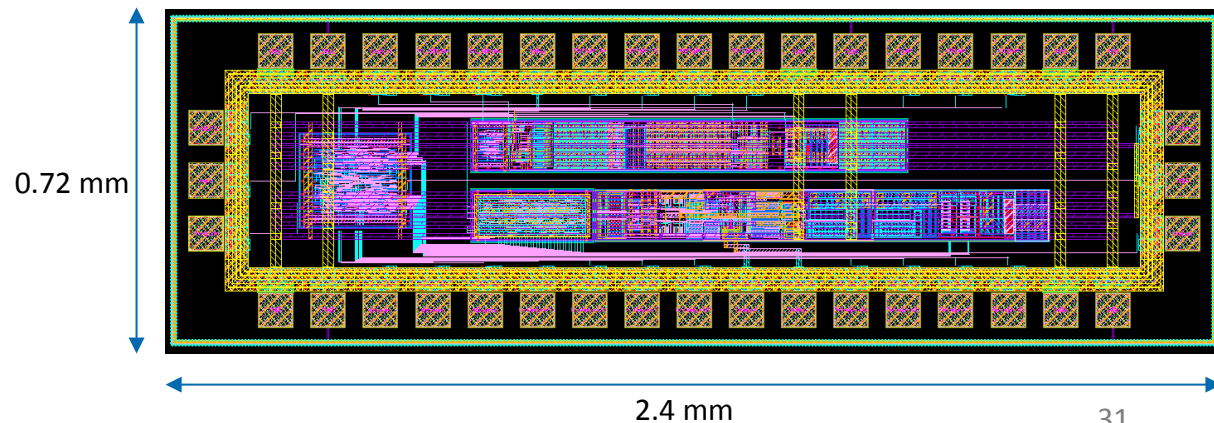
Layout  $2.32 \text{ mm} \times 0.12 \text{ mm}$

Includes PLL + Serializer + Driver + Test Features



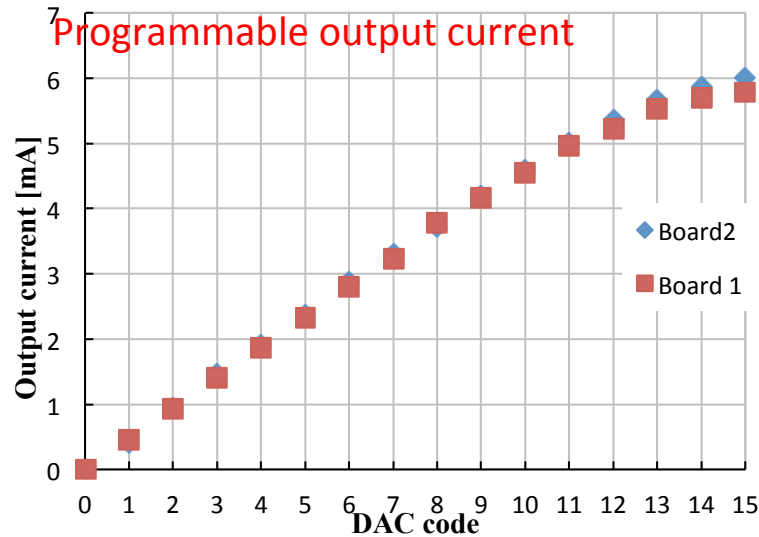
### DTU v2b Test Chip

Submitted together with  
pALPIDE-3

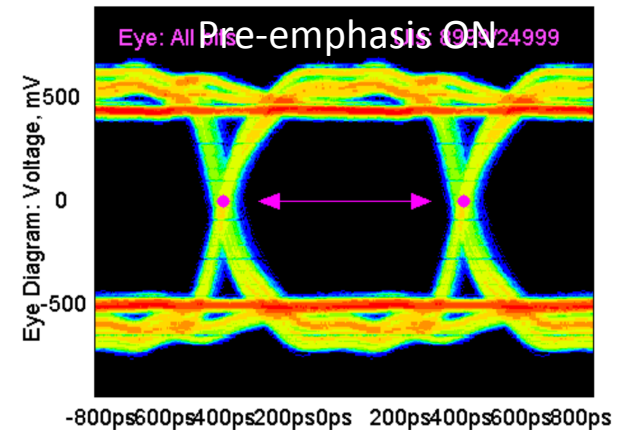
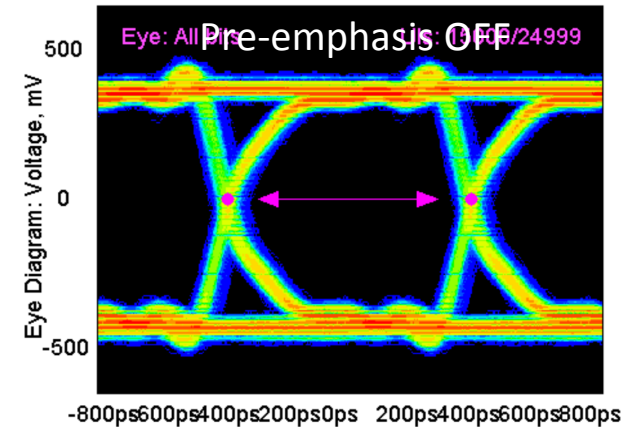


## DTU – Laboratory characterization

- **Full DTU chain functional (PLL+Serializer+Driver)**
  - Test Chip Carrier + External clock source + Coax cables + **Scope**



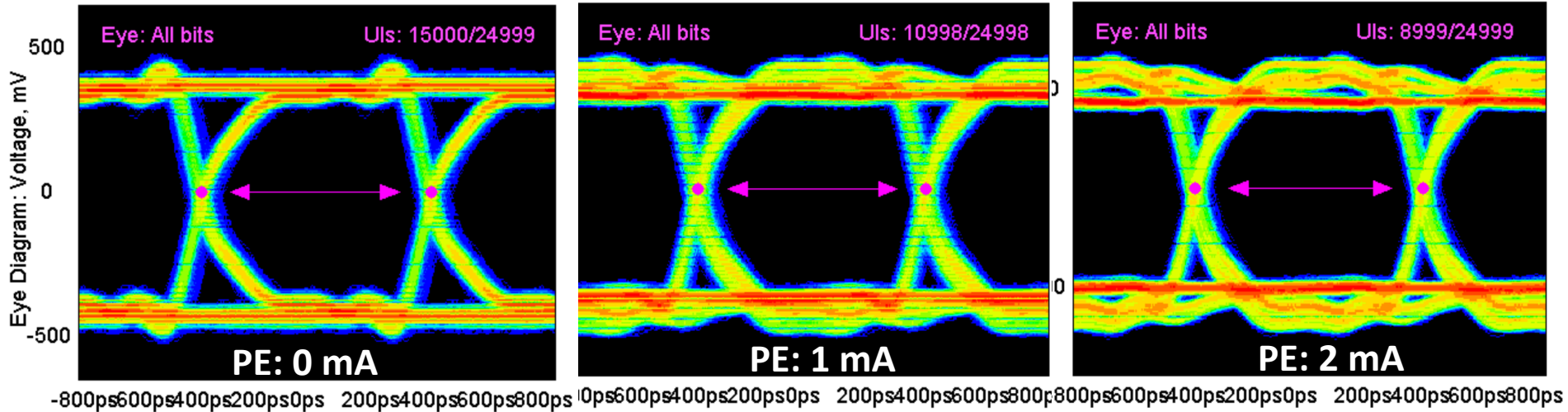
## Programmable Pre-Emphasis Current





## DTU – Laboratory characterization

### Eye diagrams vs Pre-Emphasis



Bit rate: 1.25 Gb/s

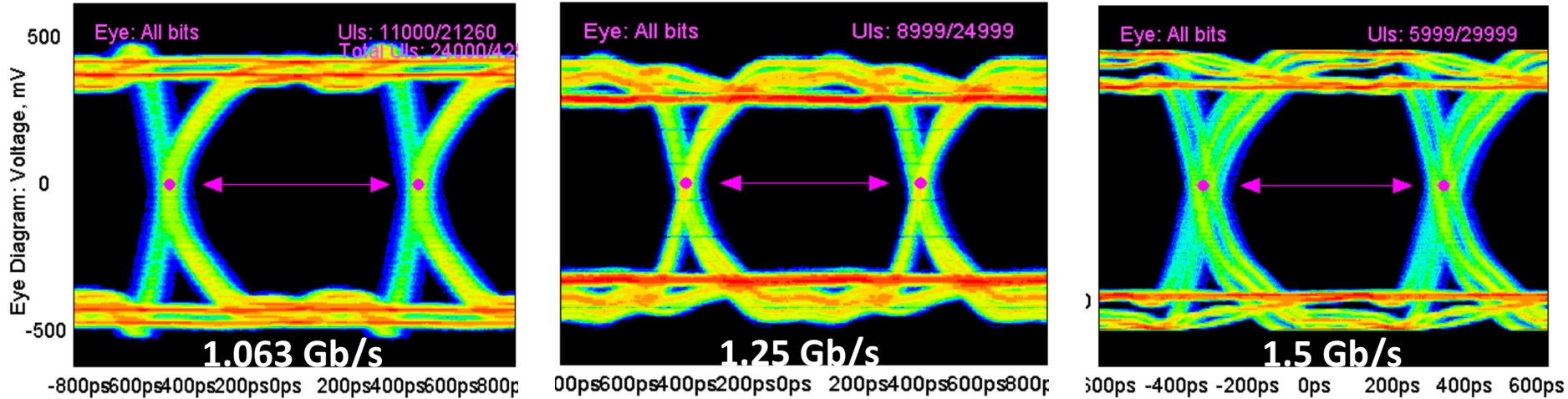
Main driver current setting: 4 mA

Pre Emphasis	0 mA	1 mA	2 mA
Eye width	0.822 UI	0.826 UI	0.835 UI
Eye opening	0.738 UI	0.742 UI	0.716 UI
Random jitter	11.4 ps	10.9 ps	12.0 ps
Deterministic jitter	48.8 ps	52.8 ps	57.4 ps

UI, Unit Interval:  $1/1.25 \text{ Gbps} = 0.8 \text{ ns}$

## DTU – Laboratory characterization

Eye diagrams vs Bit Rate



Nominal (mid range) settings for main driver current and pre-emphasis current

	1.25 Gb/s	1.063 Gb/s	1.5 Gb/s
Eye width	0.835 UI	0.820 UI	0.779 UI
Eye opening	0.716 UI	0.713 UI	0.707 UI
Random jitter	12.0 ps	13.5 ps	8.0 ps
Deterministic jitter	57.4 ps	64.6 ps	82.6 ps